



Negative Magnetoresistance in High-Mobility Heterostructures

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Dr. Lina Bockhorn

Dr. Eddy Rugeramigabo

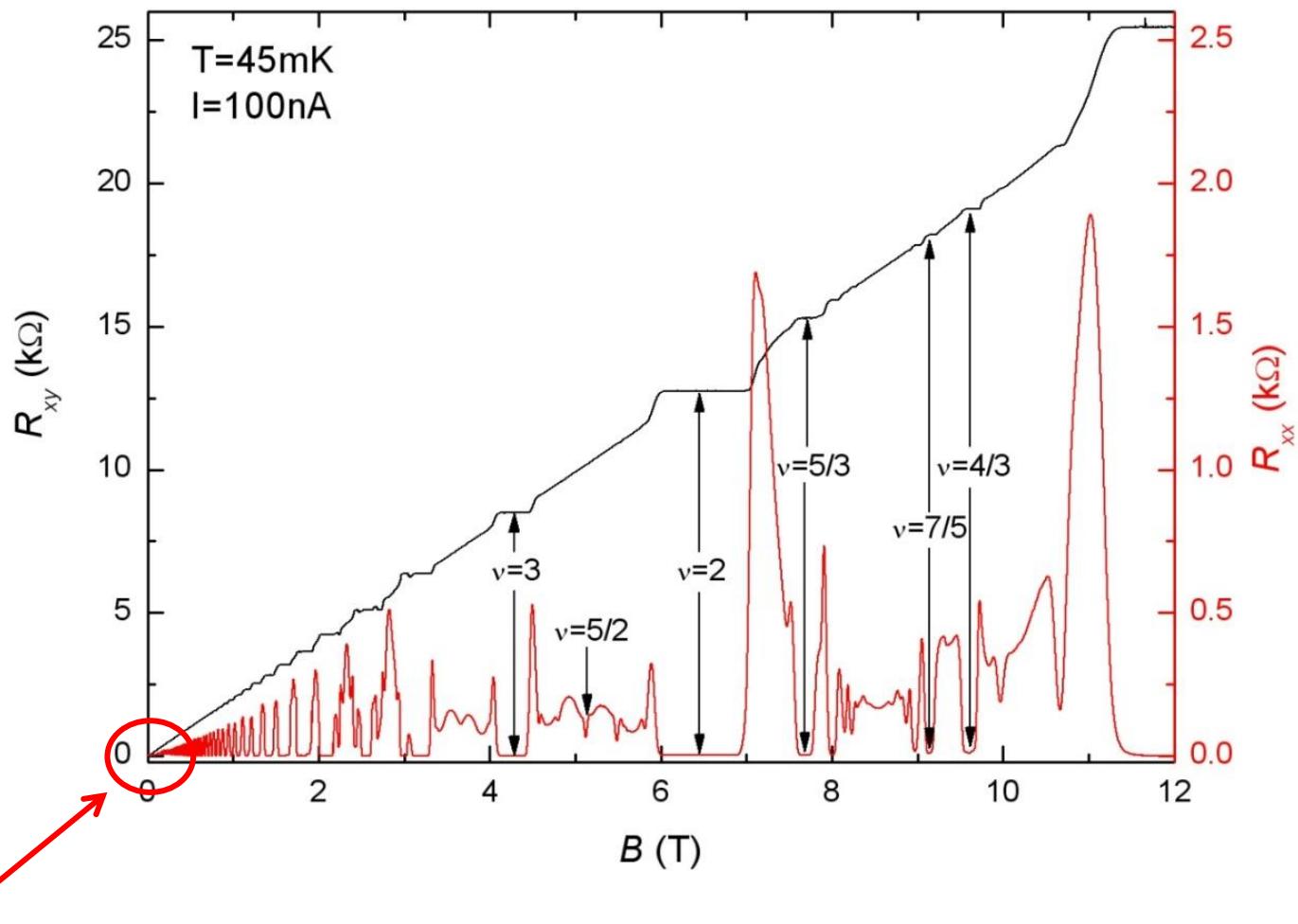


Shirin Hakim

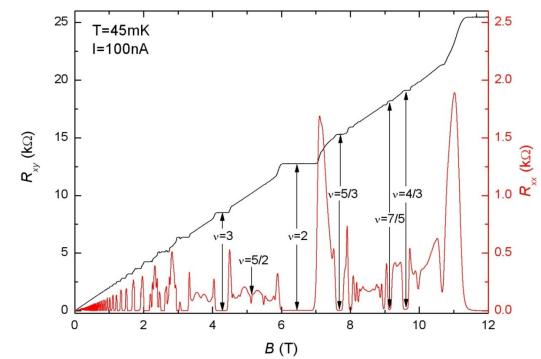
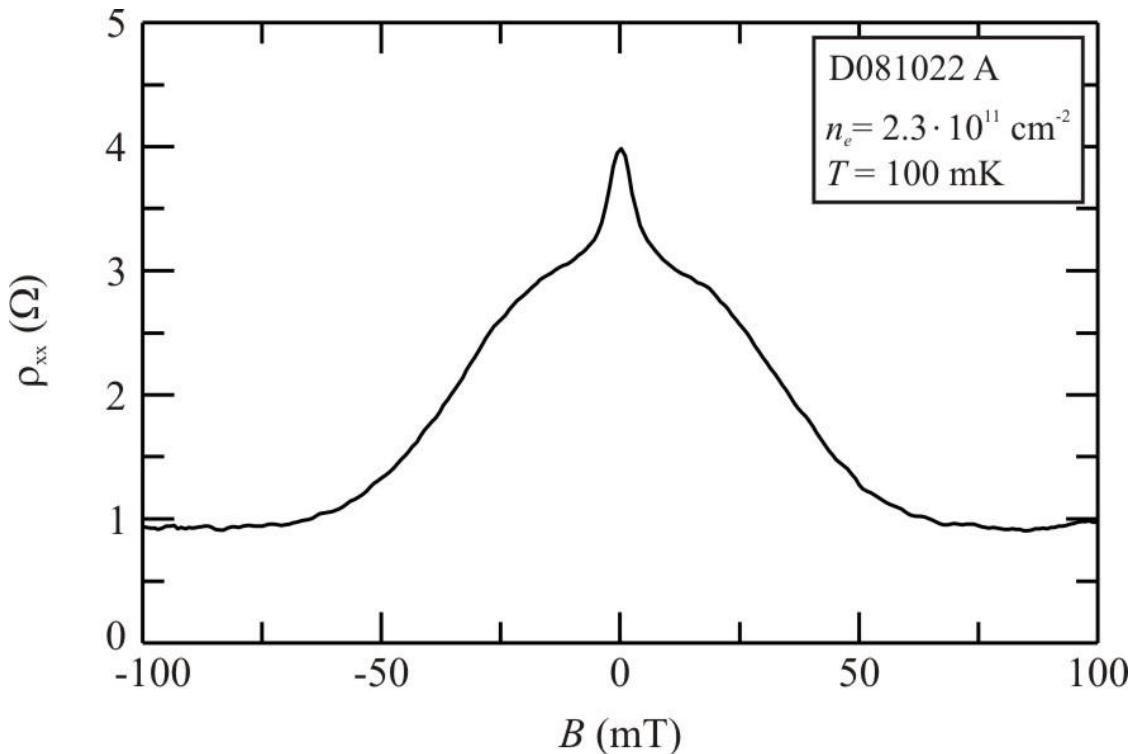
Asija Velieva

High-mobility samples:
Prof. Werner Wegscheider (Zürich)
Dr. Dieter Schuh (Regensburg)

Theory contributions:
Dr. Igor Gornyi (Karlsruhe)
Prof. Jesus Inarrea (Madrid)



Magnetoresistance in High-Mobility Sample.



Phys. Rev. B. 83, 113301 (2011)

apparently several groups had observed such strange magnetoresistance curves
(e.g. Umansky et al. APL 71, 683 (1997), Dai et al. PRL (2010)),
but no detailed investigations and no explanations

In the meantime several other experimental observations

Names for Negative Magnetoresistances

L. Bockhorn, P. Barthold, D. Schuh, W. Wegscheider, and
R. J. Haug, Phys. Rev. B 83, 113301 (2011).

huge

A. T. Hatke, M. A. Zudov, J. L. Reno, L. N. Pfeiffer, and
K. W. West, Phys. Rev. B 85, 081304 (2012).

giant

R. G. Mani, A. Kriisa, and W. Wegscheider,
Scientific Reports 3, 2747 (2013).

giant

Q. Shi, P. D. Martin, Q. A. Ebner, M. A. Zudov, L. N. Pfeiffer,
and K. W. West, Phys. Rev. B 89, 201301(R) (2014).

colossal

L. Bockhorn, I. V. Gornyi, D. Schuh, C. Reichl, W.
Wegscheider, and R. J. Haug, Phys. Rev. B 90, 165434 (2014).

giant (rare)

Q. Shi, M. A. Zudov, L. N. Pfeiffer, and K. W. West,
Phys. Rev. B 90, 201301 (2014).

colossal

L. Bockhorn, J. Inarrea, and R.J. Haug, arXiv 1504.00555

huge

Overview

- negative magnetoresistances
- magnetoresistance due to oval defects
- current-induced negative magnetoresistance
- size dependence
- conclusions

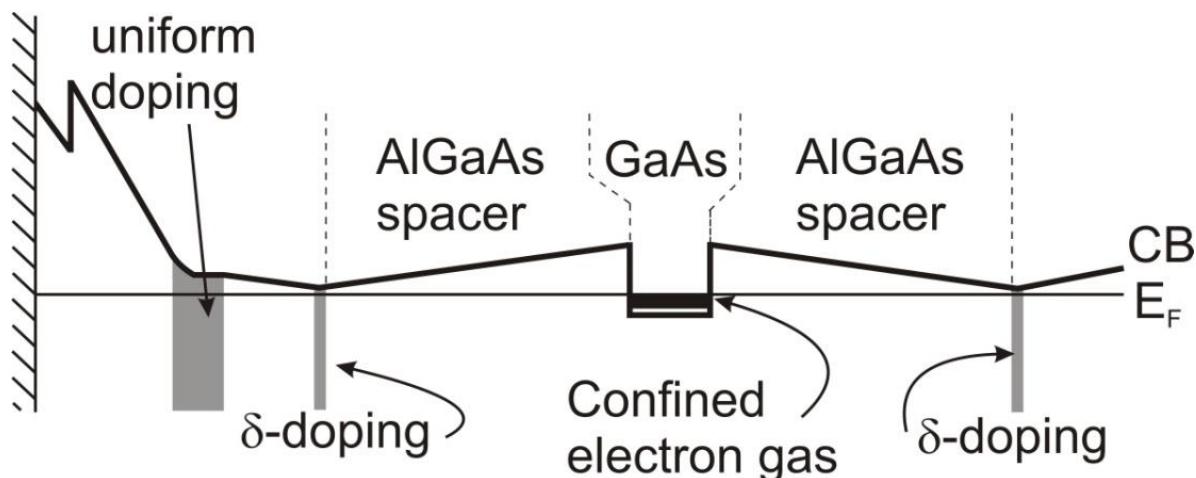
Sample Structure

GaAs/AlGaAs heterostructure:

- 30 nm quantum well (QW)
- QW located 150 nm beneath the surface
- spacer width 70 nm

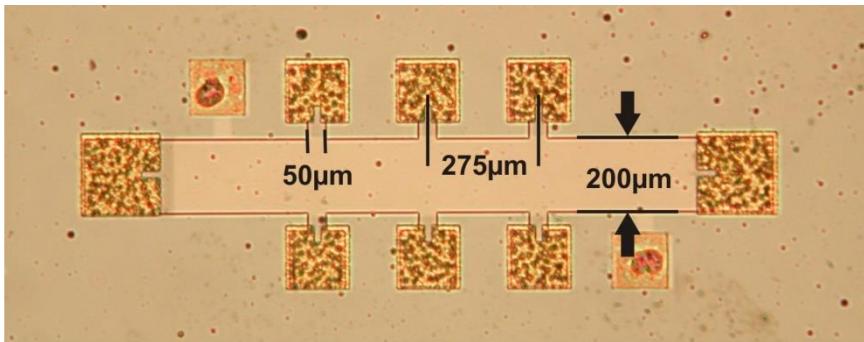
2DEG-Parameter : $n_e = 3.2 \cdot 10^{11} \text{ cm}^{-2}$

$$\mu_e = 11.9 \cdot 10^6 \text{ cm}^2/\text{Vs}$$

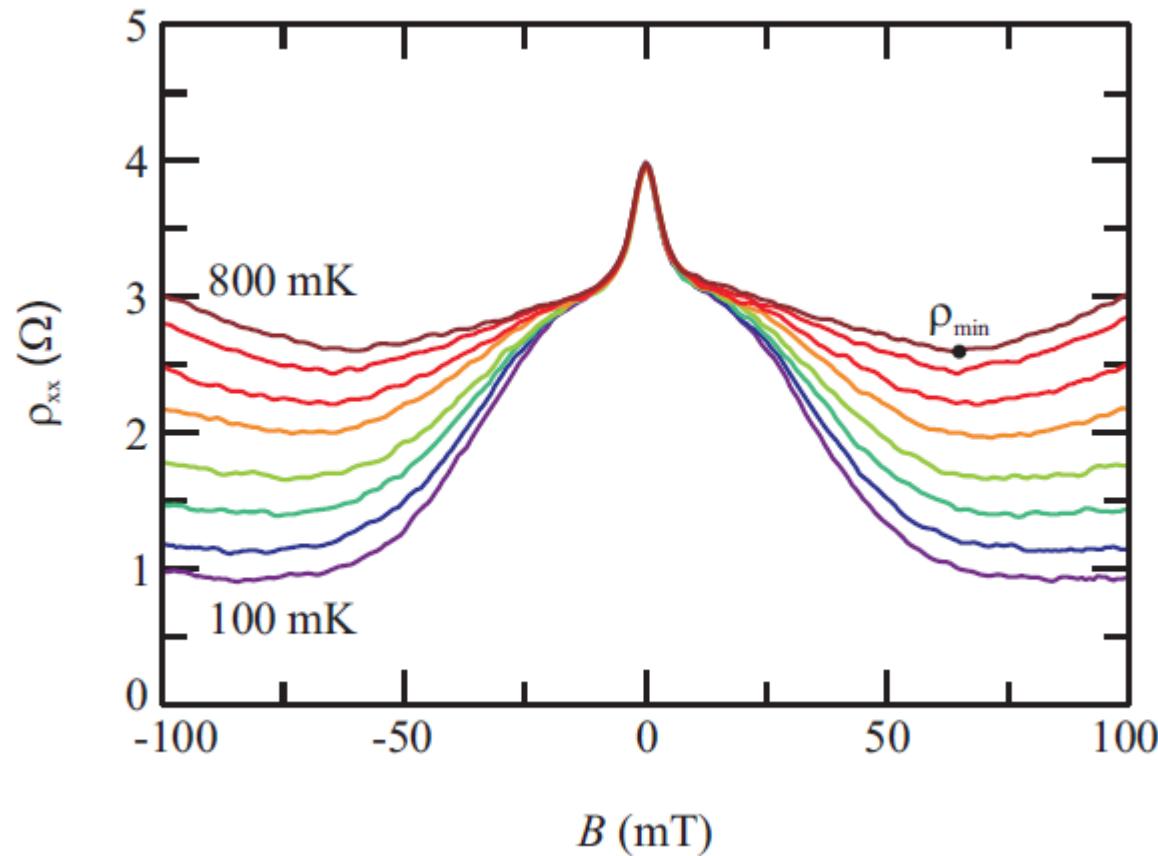


Main Geometry

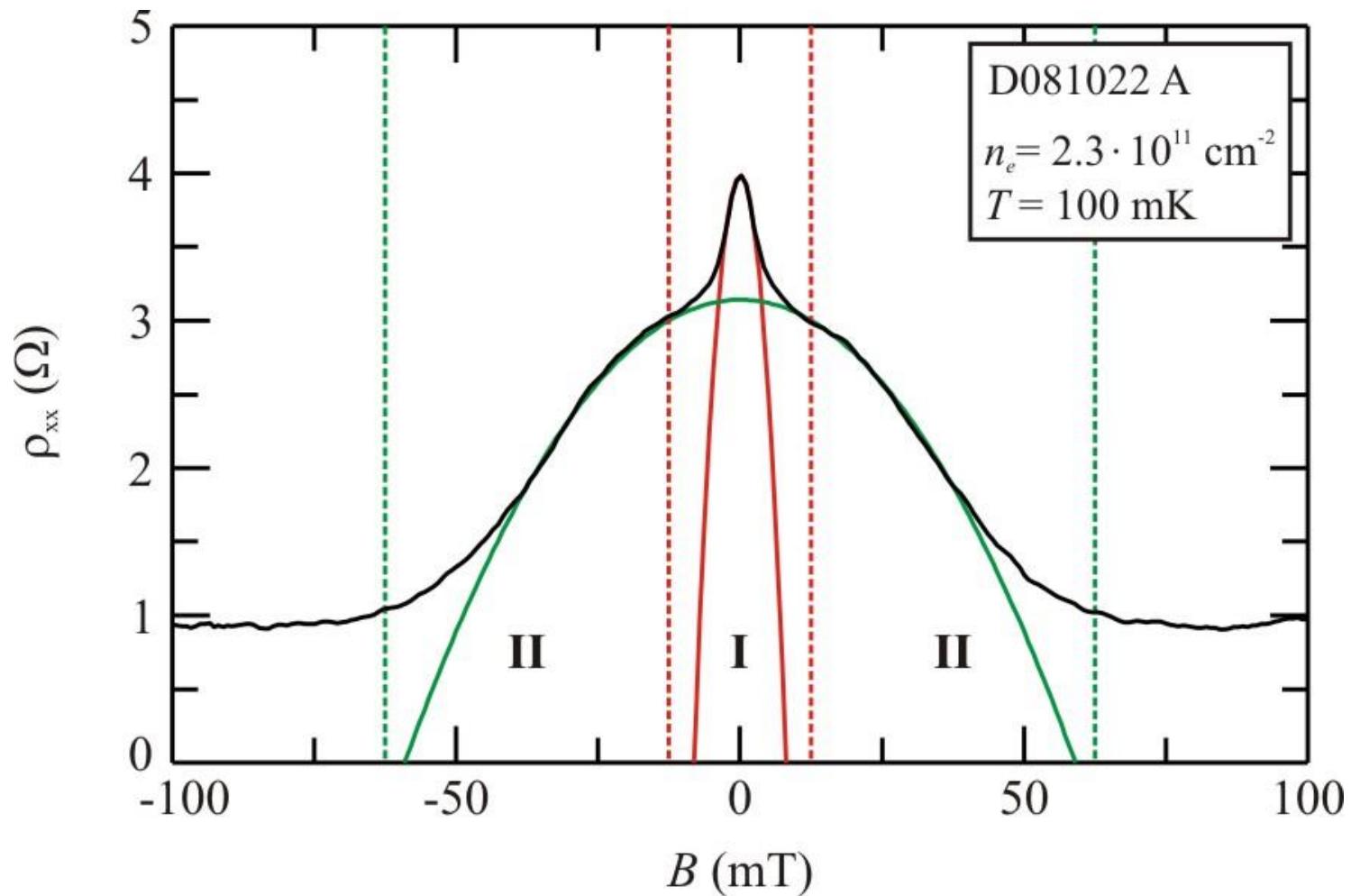
- Hall bars were defined by photolithography and wet etching
- n_e and μ_e are manipulated by using a top gate
- Hall bar dimensions are in the range of the mean free path
 - $n_e = 3.2 \cdot 10^{11} \text{ cm}^{-2}$
 - $\mu_e = 11.9 \cdot 10^6 \text{ cm}^2/\text{Vs}$
 - $\Lambda = 113 \text{ } \mu\text{m}$



Basic Facts: Temperature Dependence at Low Temperatures

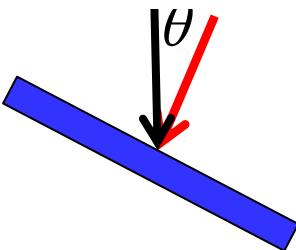
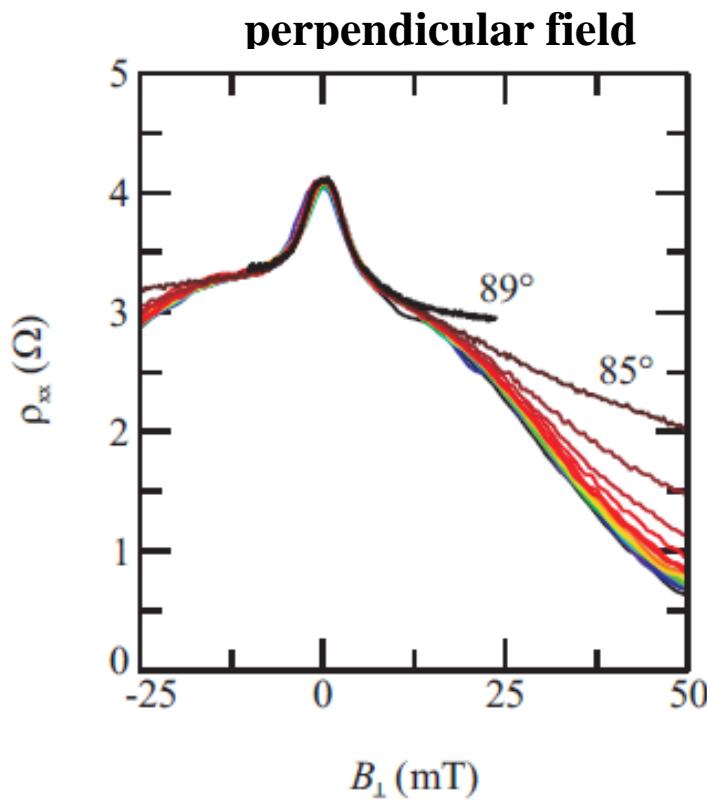
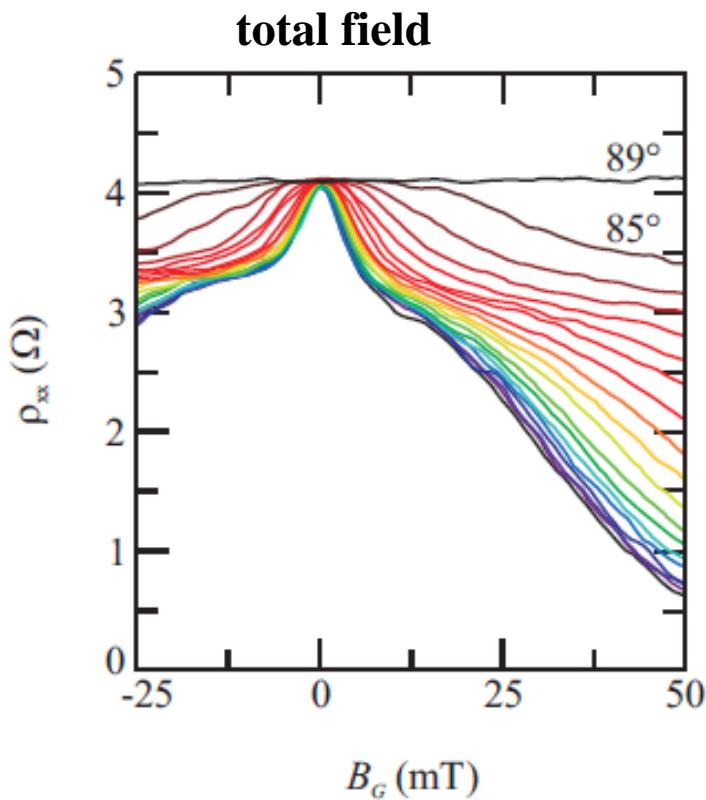


Two Different Magnetoresistances

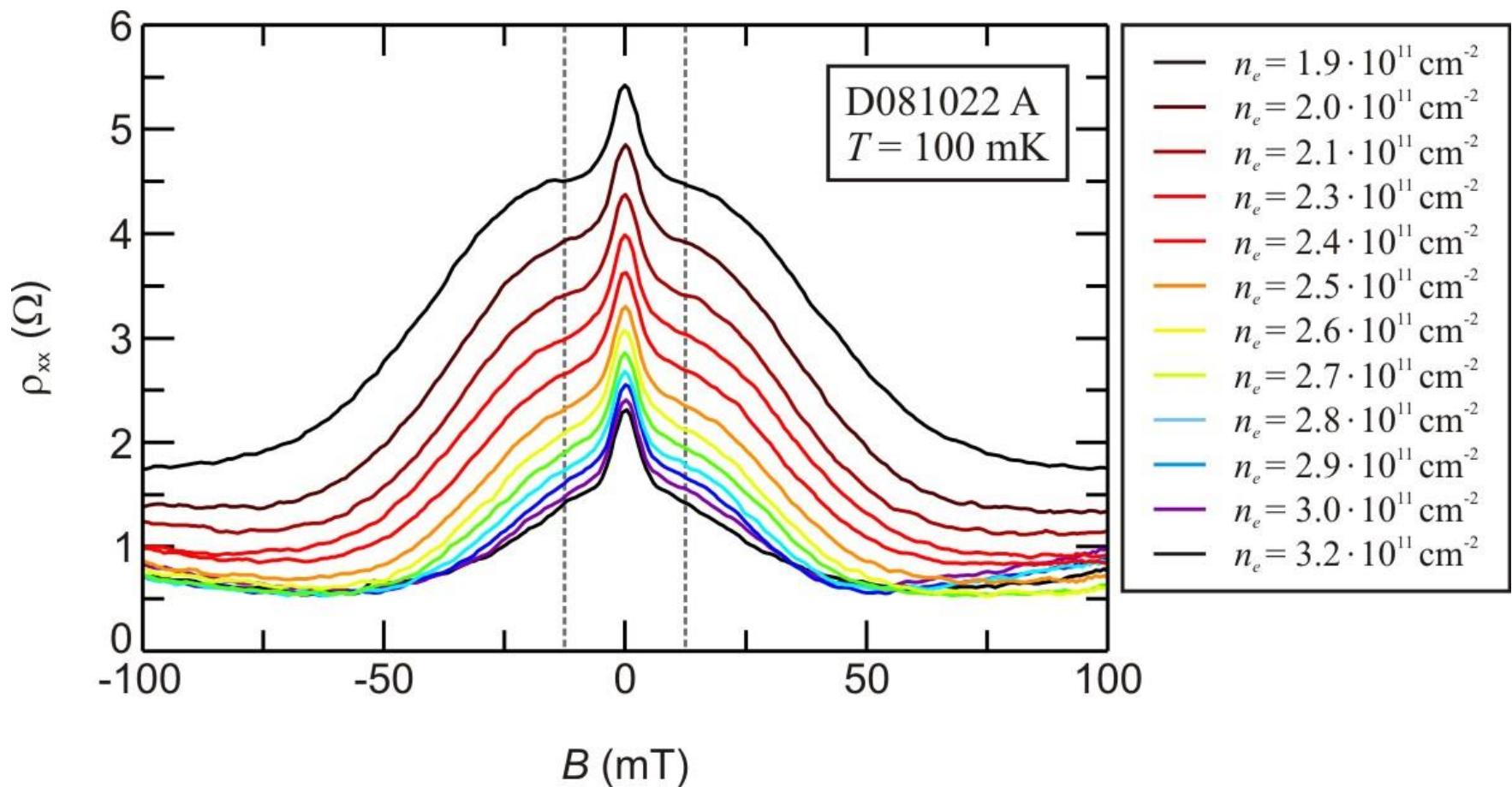


both are parabolic in field

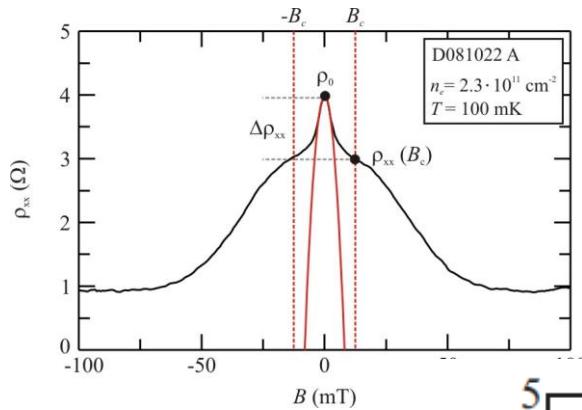
Tilted Magnetic-Field Dependence



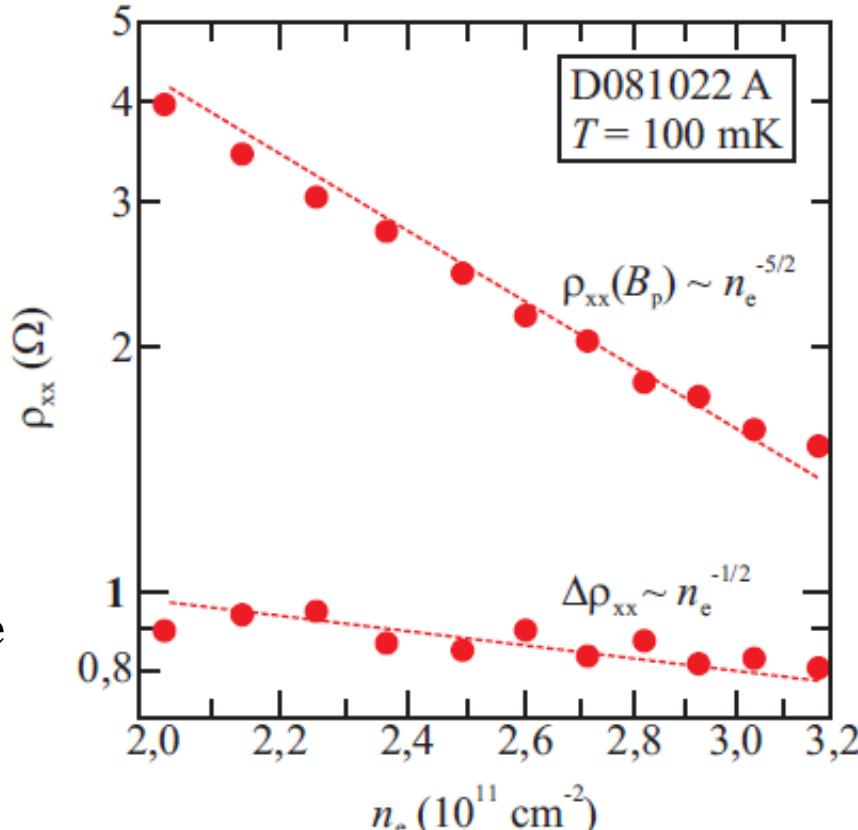
Top Gate: Density Dependence



Density Dependence of Resistances



magnetic field quenches different contributions to longitudinal resistance



additional type
of disorder

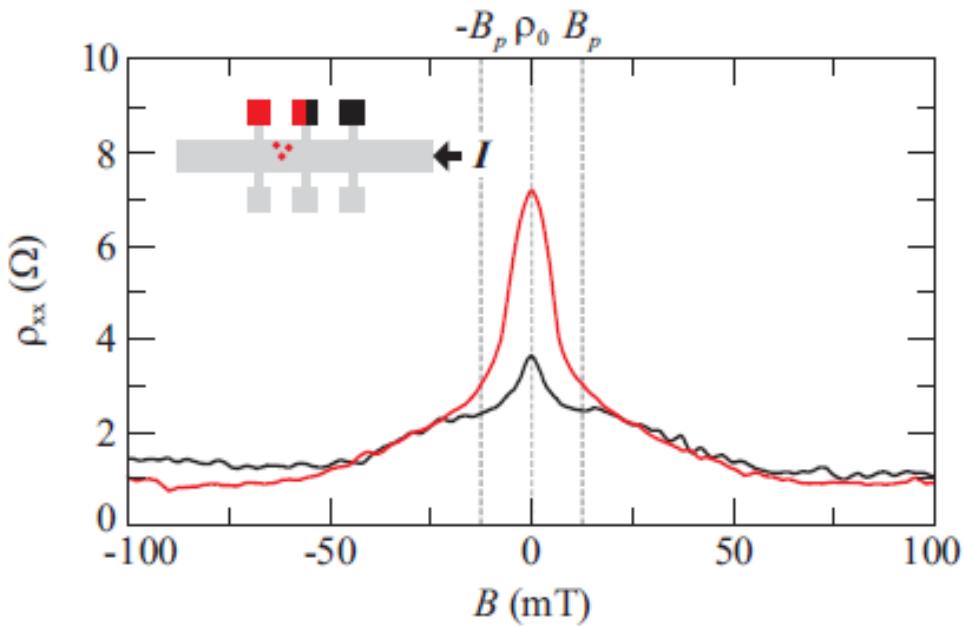
scattering from
smooth disorder
(remote ionized
impurities)

Small Peak

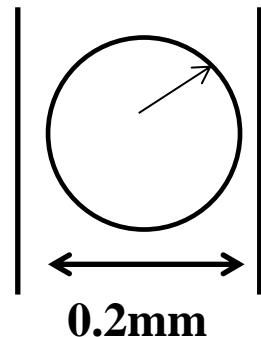
- temperature independent below 1 K
- depends only on perpendicular magnetic field: two dimensional

→ classical effect

- not always small

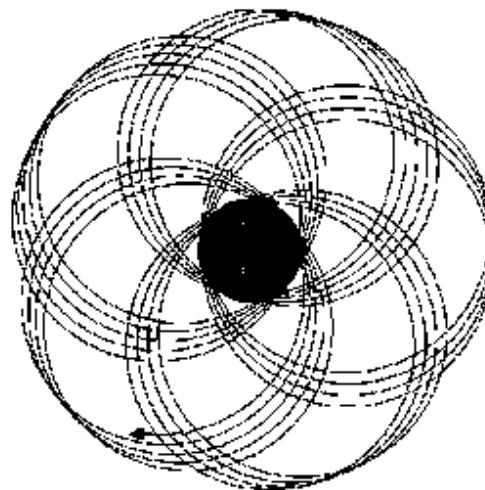


e.g.
classical cyclotron radius
of 0.1mm
at 0.7mT
???



Quasiclassical magnetotransport in a random array of antidots

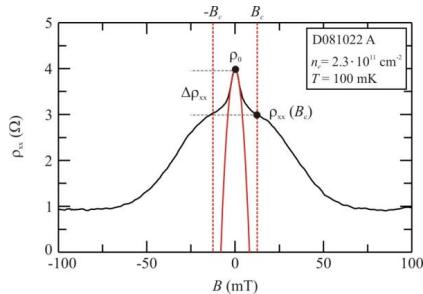
D. G. Polyakov,^{1,*} F. Evers,¹ A. D. Mirlin,^{1,2,†} and P. Wölfle^{1,2}



see also:

E.M. Baskin, L.I. Magarill, and M.V. Entin, Zh. Eksp. Teor. Fiz. 75, 723 (1978) [Sov. Phys. JETP 48, 365 (1978)]; E.M. Baskin and M.V. Entin, Physica B 249-251, 805 (1998).

Interplay of Strong Scatterers and Smooth Disorder: Classical Memory Effect



situation for high-mobility structures

$$\tau_S \sim \tau_L \quad (\omega_0 \sim \omega_{perc})$$

τ_S transport scattering time for strong scatterers

τ_L transport scattering time for smooth disorder

$$\frac{\rho_{xx}}{\rho_0} = 1 - \frac{\omega_c^2}{2\pi n_S v_F^2} f(x) \quad x = \tau_S / \tau_L$$

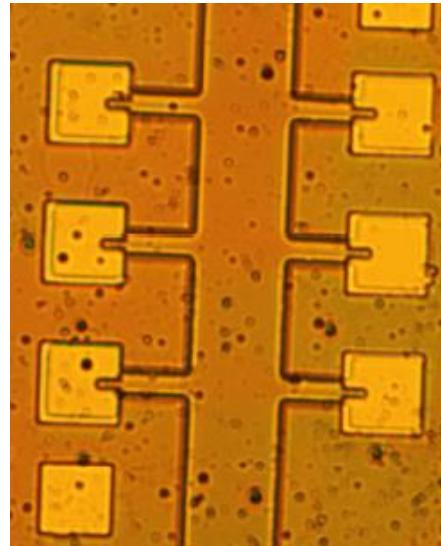
$$1 - 10 \cdot 10^4 \text{ cm}^{-2}$$

very low density of strong scatterers
radius: $10 - 20 \mu\text{m}$

$$f(x) = \frac{2}{x+1} \int_0^\infty dq \frac{q J_1^2(q)}{x q^2 + 2[1 - J_0^2(q)]}$$

L. Bockhorn et al.
Phys. Rev. B 90, 165434 (2014)

Sample Surfaces



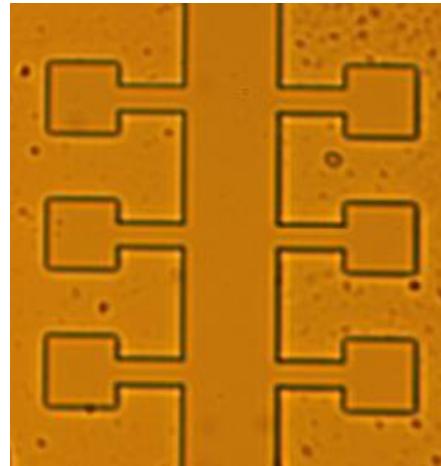
macroscopic defects seen at the surface

diameter: up to $40\mu\text{m}$

density: around 10^4 cm^{-2}

→ inter-defect spacing: $d_{OD} \sim 90 \mu\text{m}$

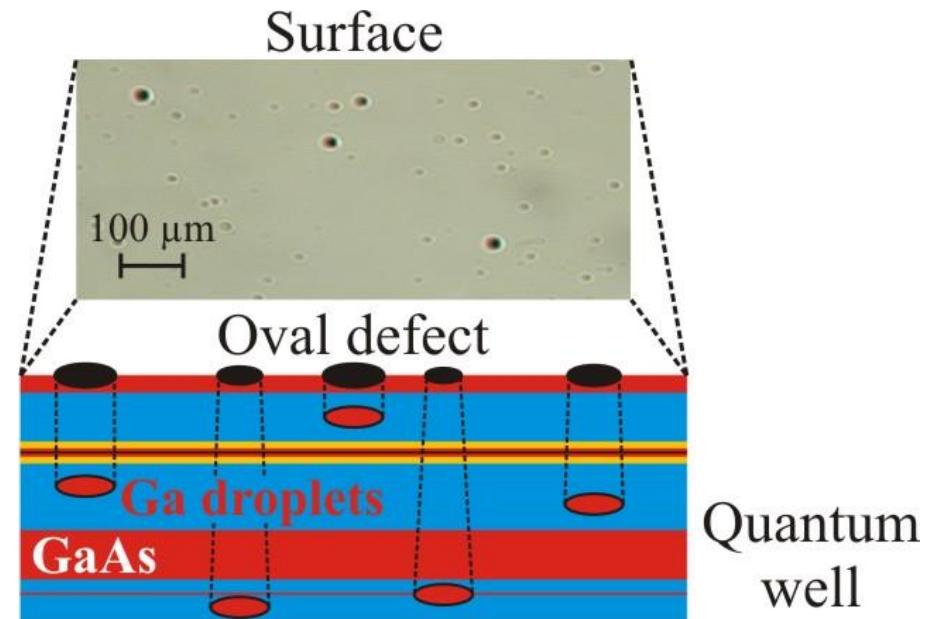
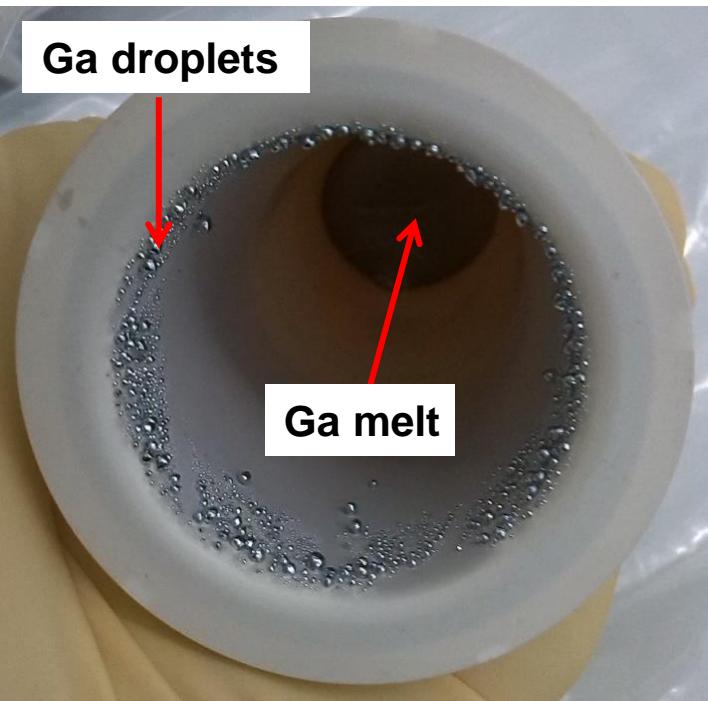
- oval defects are always present!



$$\rightarrow l \sim d_{OD}$$

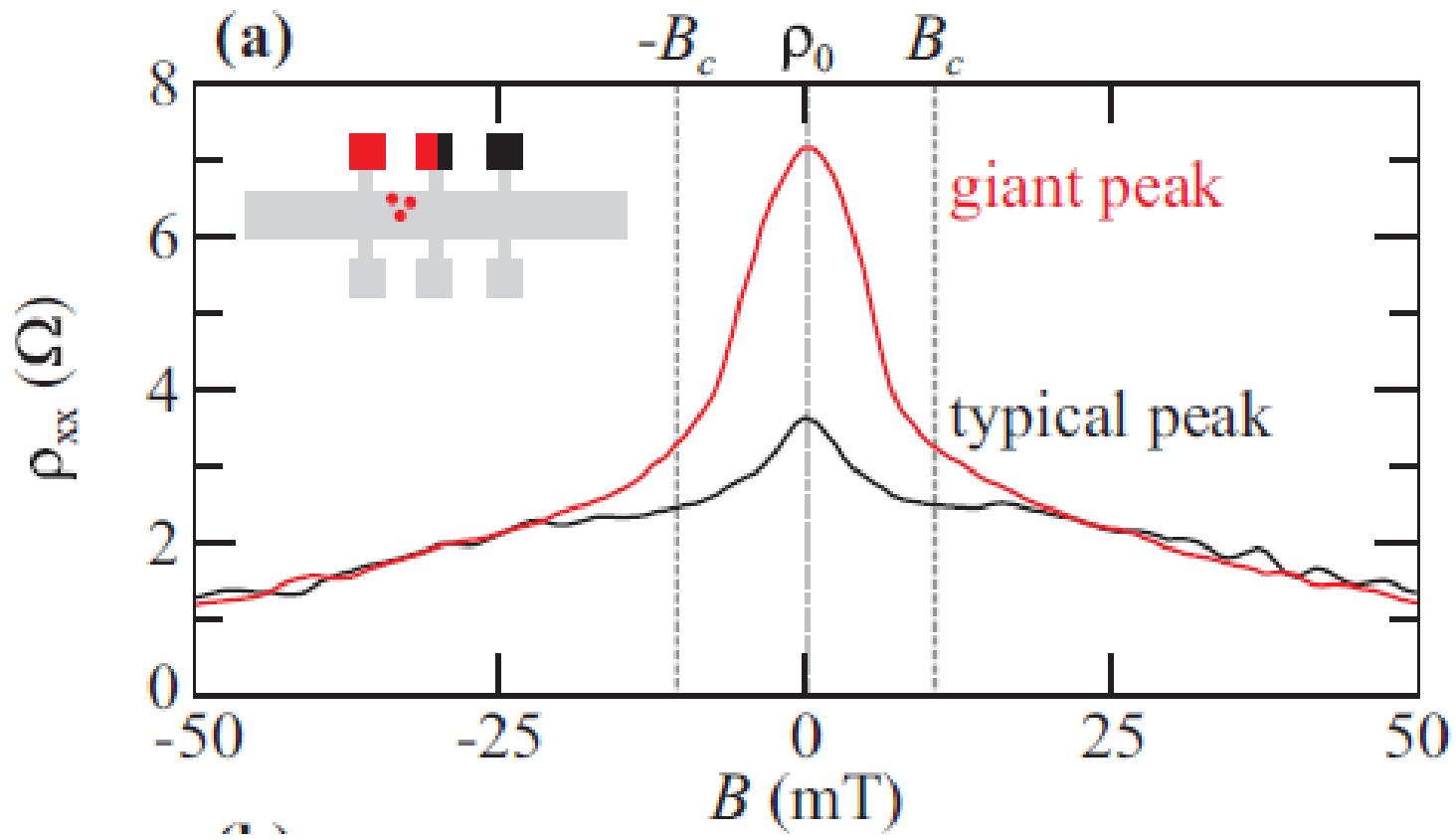
$$\rightarrow \mu \sim 1 \times 10^7 \text{ cm}^2/\text{Vs}$$

Oval Defects in the Sample

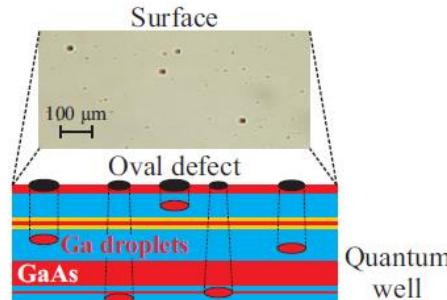


- Y. G. Chai and R. Chow, *Appl. Phys. Lett.* **38**, 796 (1981).
G. D. Pettit, J. M. Woodall, S. L. Wright, P. D. Kirchner, and J. L. Freeouf, *J. Vac. Sci. Technol. B* **2**, 241 (1984).
K. Akimoto, M. Dohsen, M. Arai, and N. Watanabe, *J. Cryst. Growth* **73**, 117 (1985).
S.-L. Weng, *Appl. Phys. Lett.* **49**, 345 (1986).
M. Shinohara and T. Ito, *J. Appl. Phys.* **65**, 4260 (1989).

Different Densities of Oval Defects = Different Peak Heights

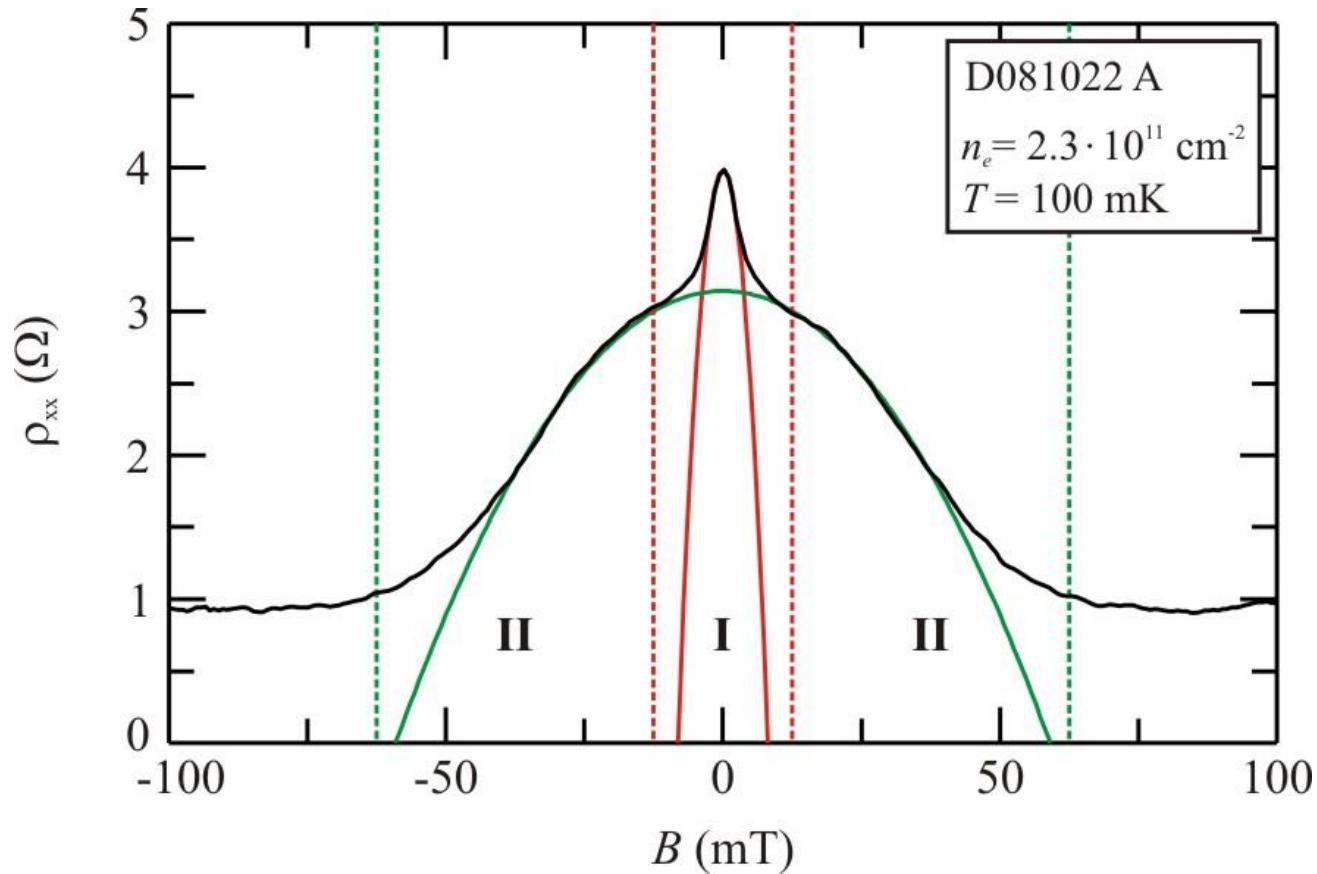


L. Bockhorn et al.
Phys. Rev. B 90, 165434 (2014)



Leibniz
Universität
Hannover

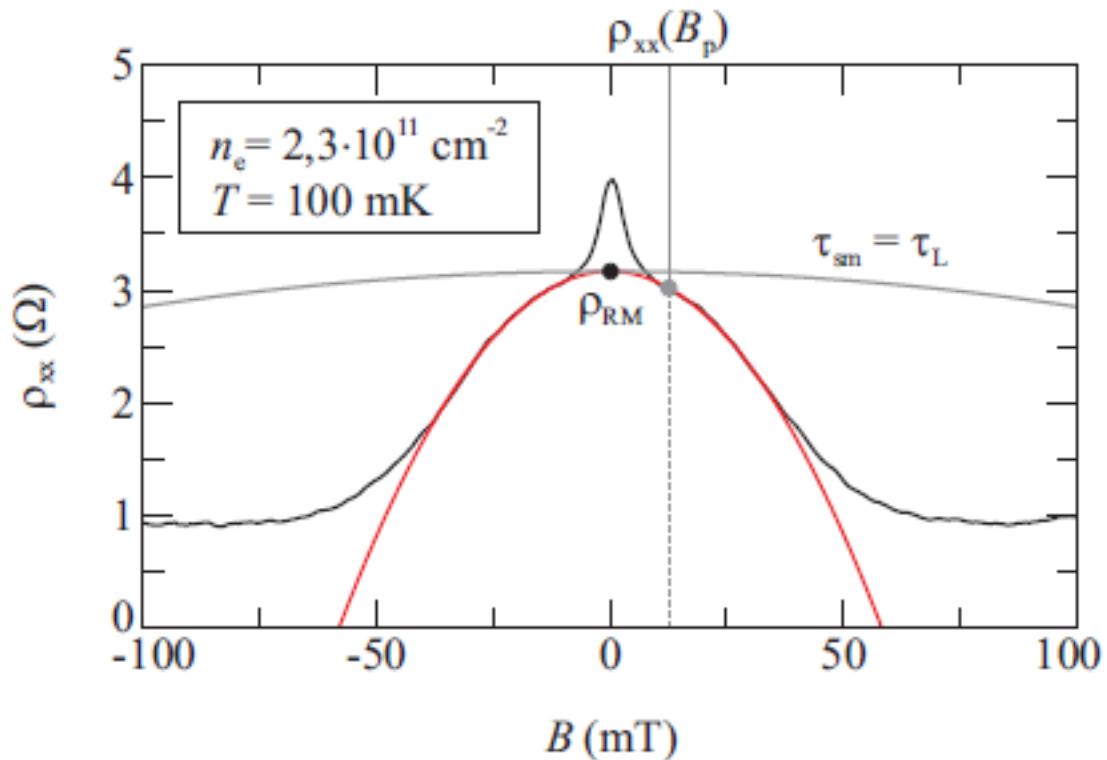
Huge Peak



temperature dependent, parallel field dependent

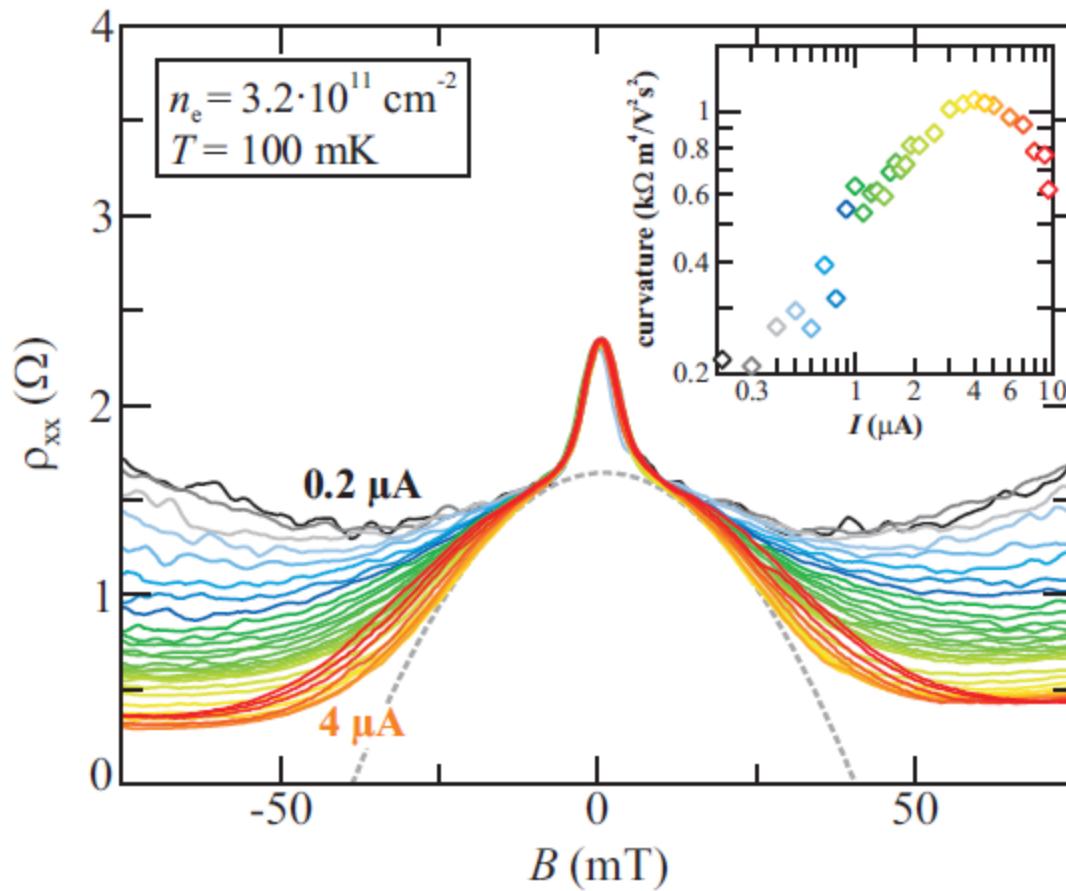
Electron-Electron Interaction Correction in the Ballistic Regime

$$\rho_{xx} = \frac{1}{\sigma_0} + \frac{1}{\sigma_0^2} (\mu^2 B^2) [\delta\sigma_{xx}^{ee}(T)]^{-1}$$



I.V. Gornyi, A.D. Mirlin,
Phys. Rev. Lett. 90, 076801 (2003)

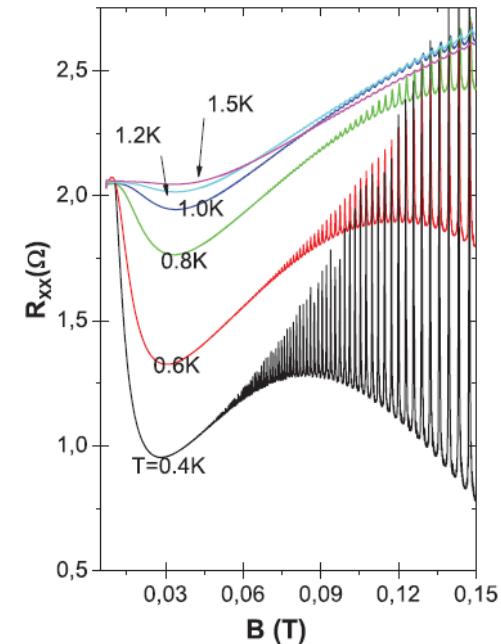
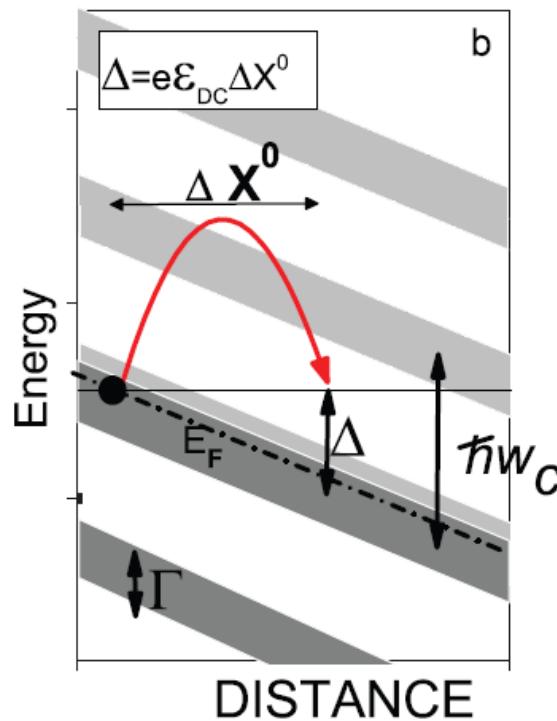
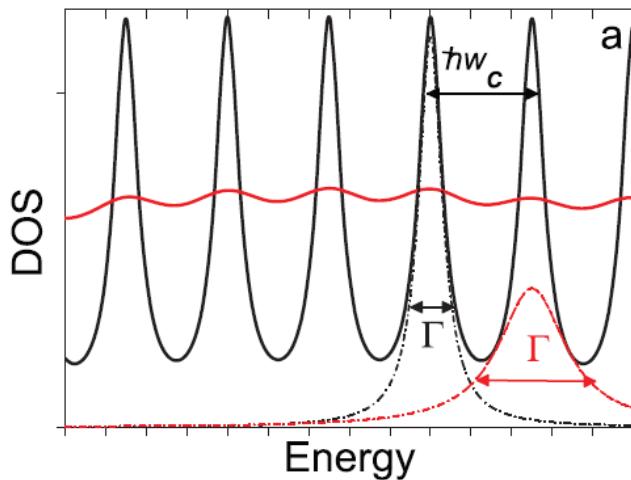
Current-Induced Negative Magnetoresistance



arXiv 1504.00555

Theoretical model for negative giant magnetoresistance in ultrahigh-mobility 2D electron systems

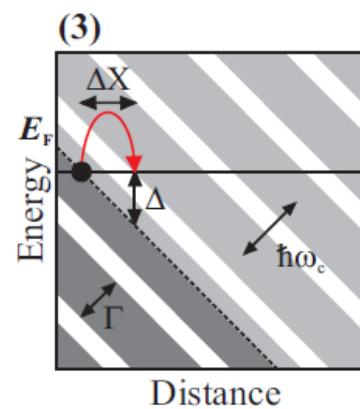
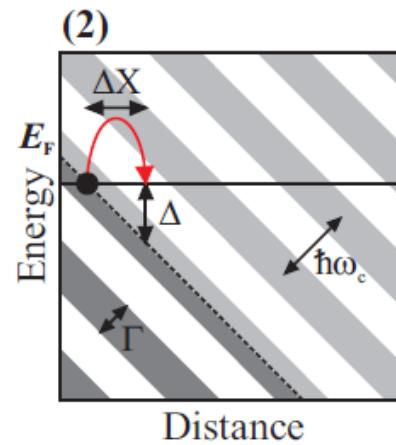
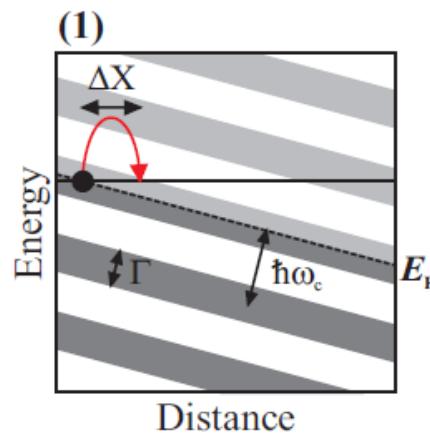
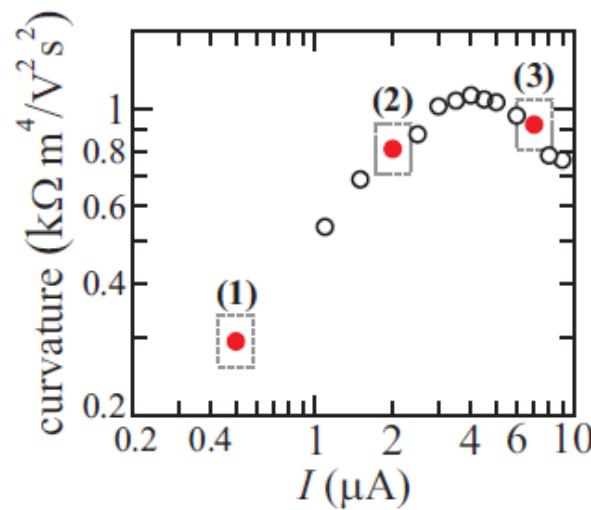
J. IÑARREA



Analogous Explanation for Our Results

$$\varpi_c \tau = 1$$

at $B = 0.86\text{mT}$



arXiv 1504.00555

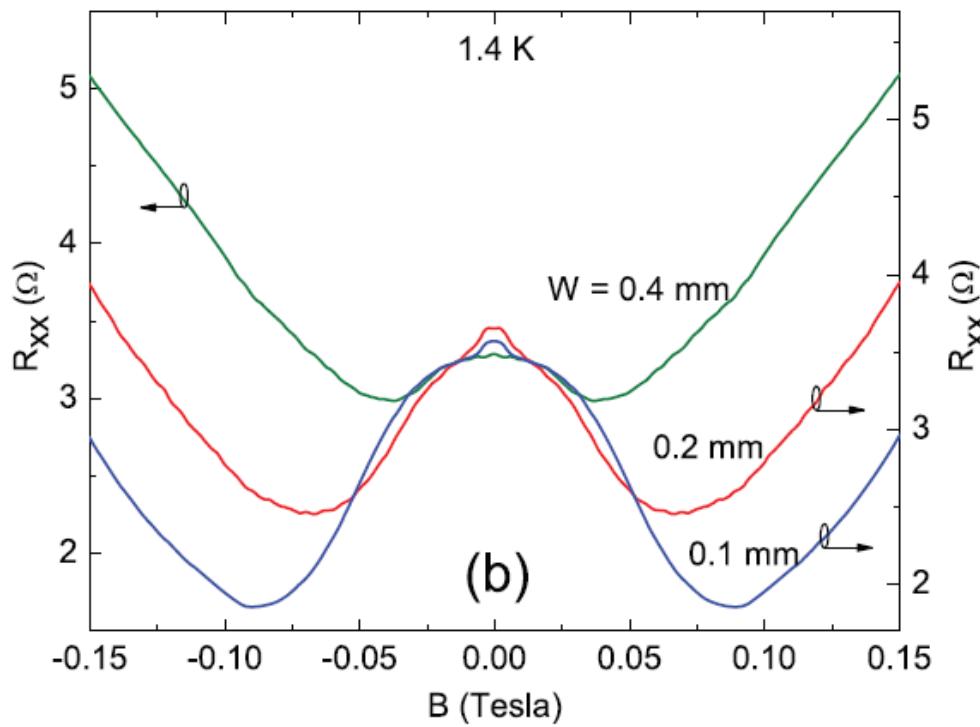
Size Dependence?

L. Bockhorn, A. Hodaei, D. Schuh, W. Wegscheider, and
R. J. Haug, *J. Phys.: Conf. Ser.* **456**, 012003 (2013).

presentation at high-magnetic field conference in Chamonix 2012

small peak is not geometry dependent, huge peak shows geometry dependence

Size Dependence



R. G. Mani¹, A. Kriisa² & W. Wegscheider³

SCIENTIFIC REPORTS | 3 : 2747 | DOI: 10.1038/srep02747

2013

Conclusions

- negative magnetoresistances
in high-mobility 2DEGs
- small peak: classical effect
due to scattering from oval defects
- huge peak:
temperature dependent
current induced
- size dependence?

